ABSTRACT OF THE DISCLOSURE

Semiconductor device 3 comprises semiconductor chip
11, Au ball bumps 21 formed on pad electrodes 12 with a
stud bump method, and thermoplastic adhesive layer 22
provided on the surface of semiconductor chip 11 on which
pad electrodes 12 are formed, in which the tops of Au
ball bumps 21 project from the surface of adhesive layer
22. Reliable bonding can be realized by forming the bumps
for electrical connection and the adhesive resin having
an adhesion function on the semiconductor chip. In
addition, the present invention provides a method of
bonding a copper foil to a semiconductor wafer to form a
wiring pattern, a multi chip module in which electrical
connection is established by bumps bonded to each other
through an adhesive layer, and the like.